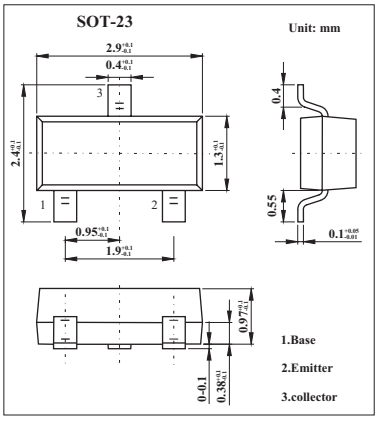
Silicon PNP Epitaxial

2SA1468



■ Features

- High voltage amplifier.

■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector to base voltage	V_{CBO}	-180	V
Collector to emitter voltage	V_{CEO}	-180	V
Emitter to base voltage	V_{EBO}	-5	V
Collector current	I_C	-100	mA
Collector power dissipation	P_C	150	mW
Junction temperature	Tj	150	℃
Storage temperature	T_{stg}	-55 to +150	℃

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector to base breakdown voltage	$V_{(BR)CBO}$	I_C = -10 μA, I_E = 0	-180			V
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	I_C = -0.5 mA, R_{BE} = ∞	-180			V
Emitter to base breakdown voltage	$V_{(BR)EBO}$	I_E = -10 μA, I_C = 0	-5			V
DC current transfer ratio	h_{FE}	V_{CE} = -12 V,I_C = -2 mA	100		320	
Collector to emitter saturation voltage	$V_{CE(sat)}$	I_C = -30 mA,I_B = -3 mA			-0.5	V
Base emitter voltage	V_{BE}	V_{CE} = -12 V, I_C = -2 mA			-1	V
Gain bandwidth product	f_T	V_{CE} = -12 V,I_C = -10 mA		200		MHz
Collector output capacitance	C_{ob}	V_{CB} = -10 V, I_E = 0,f = 1 MHz		3.5		pF

■ h_{FE} Classification

Marking	INB	INC
Rank	B	C
hFE	100～200	160～320